

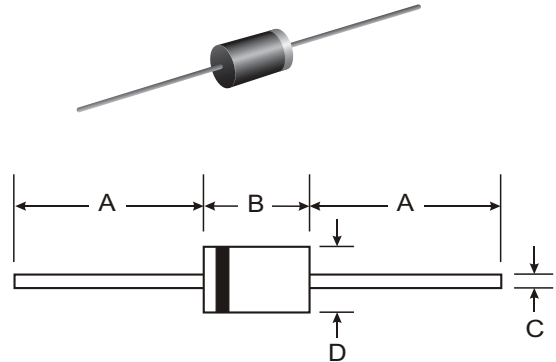
VOLTAGE RANGE: 100V
CURRENT: 1.0 A

Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

Mechanical Data

- Case: DO-41, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.34 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



DO-41		
Dim	Min	Max
A	25.40	—
B	4.06	5.21
C	0.71	0.864
D	2.00	2.72
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	SR1A0	Unit
Maximum repetitive peak reverse voltage	V_{RRM}	100	Volts
Maximum RMS voltage	V_{RMS}	70	Volts
Maximum DC blocking voltage	V_{DC}	100	Volts
Maximum average forward rectified current 0.375" (9.5mm) lead length (see fig.1)	$I_{(AV)}$	1.0	Amp
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	40.0	Amps
Maximum instantaneous forward voltage at 1.0A	V_F	0.85	Volts
Maximum DC reverse current $T_A=25^\circ\text{C}$ at rated DC blocking voltage $T_A=100^\circ\text{C}$	I_R	1.0 10.0	mA
Typical junction capacitance (NOTE 1)	C_J	80	pF
Typical thermal resistance (NOTE 2)	R_{qJA}	50.0	$^\circ\text{C/W}$
Operating junction temperature range	T_J	-65 to +150	$^\circ\text{C}$
Storage temperature range	T_{STG}	-65 to +150	$^\circ\text{C}$

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

2. Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C.B. mounted

